

TITLE: A TRENCHED GATE NON-VOLATILE SEMICONDUCTOR METHOD WITH THE
SOURCE/DRAIN REGIONS SPACED FROM THE TRENCH BY SIDEWALL DOPINGS
INVENTOR(S): Yowjuang William Liu and Donald L. Wollesen
USSN: 09/629,780 Attorney Docket #: AMD-C553397.DIV

1 / 8

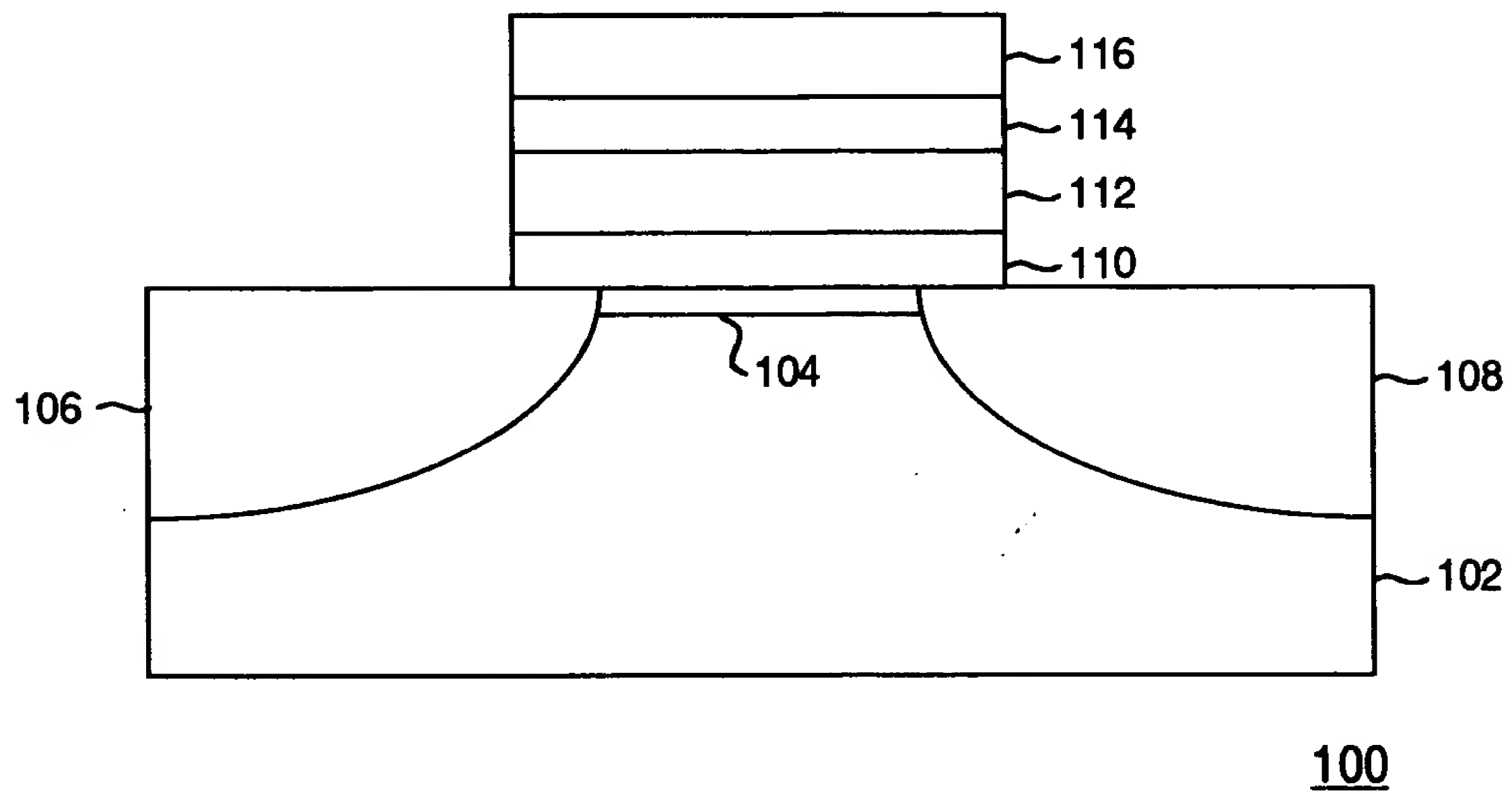


Figure 1 (Prior Art)



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2 / 8

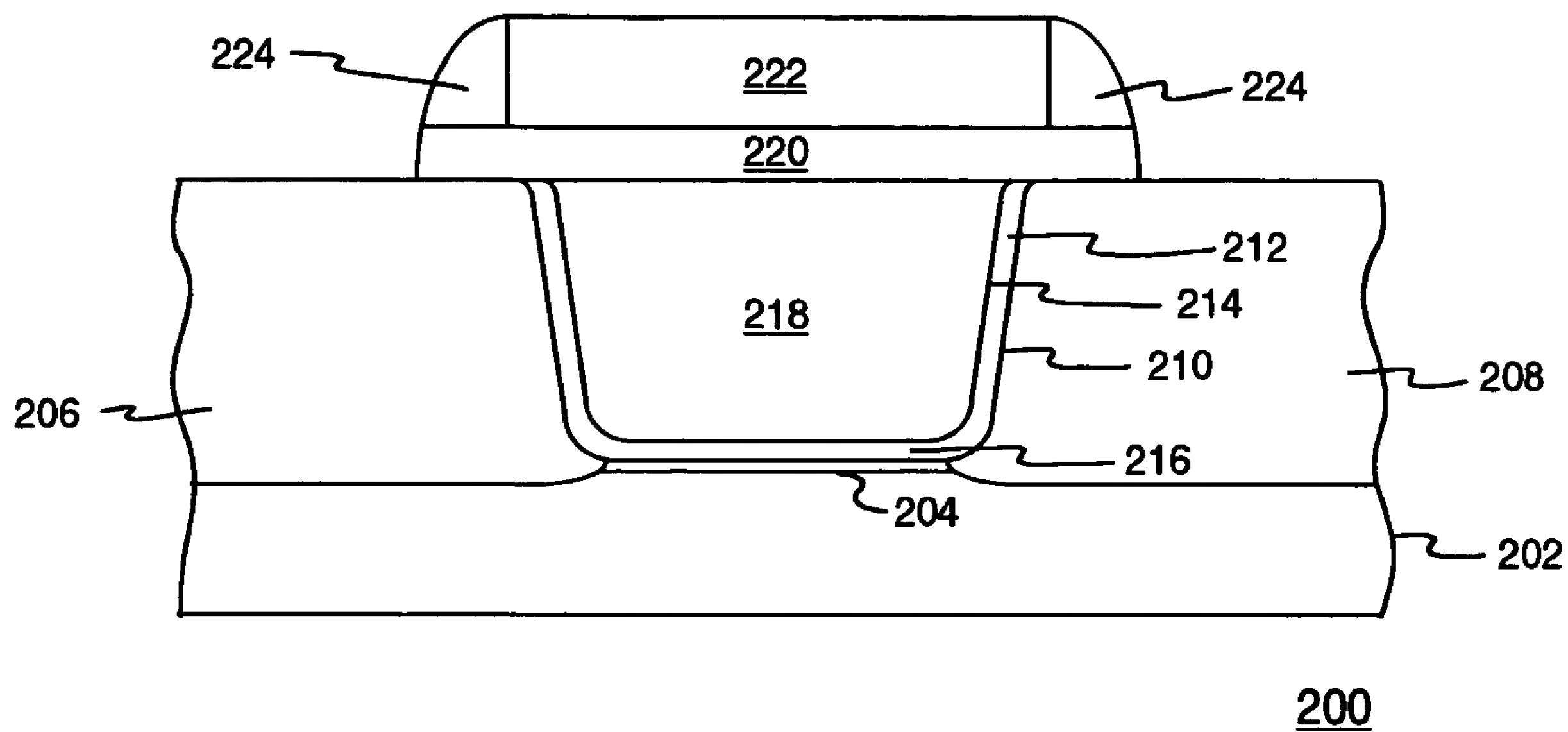


Figure 2A

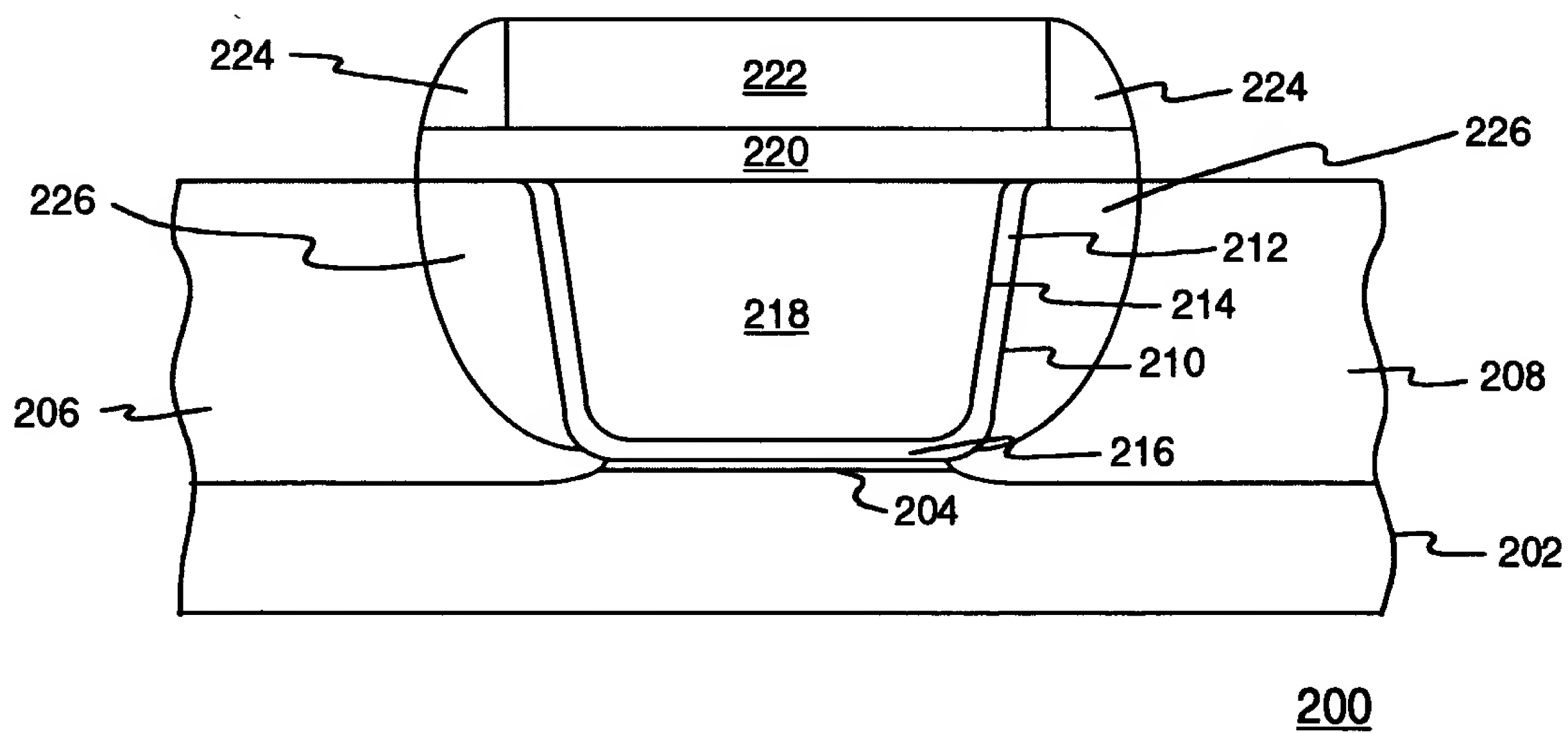


Figure 2B

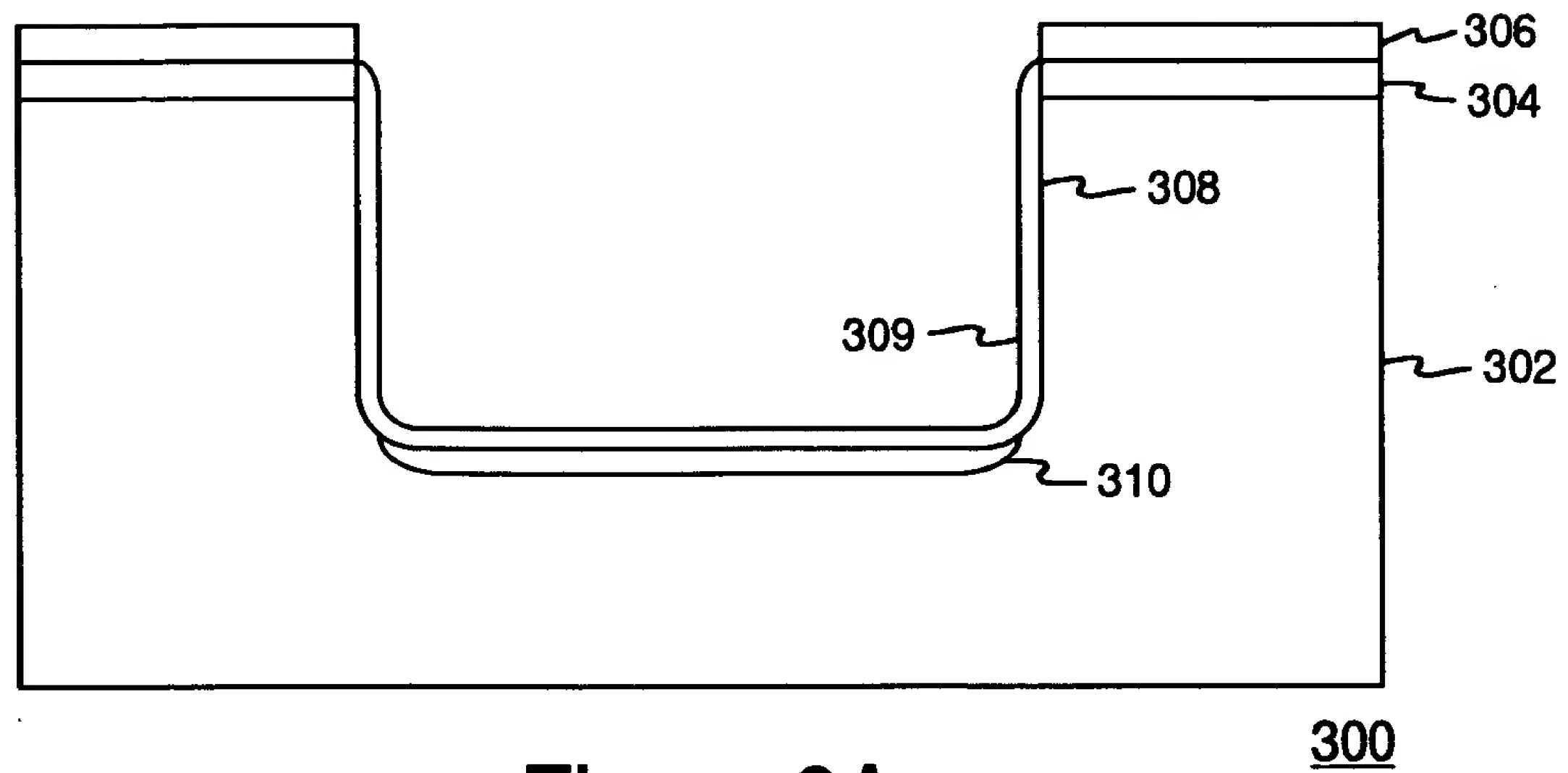


Figure 3A

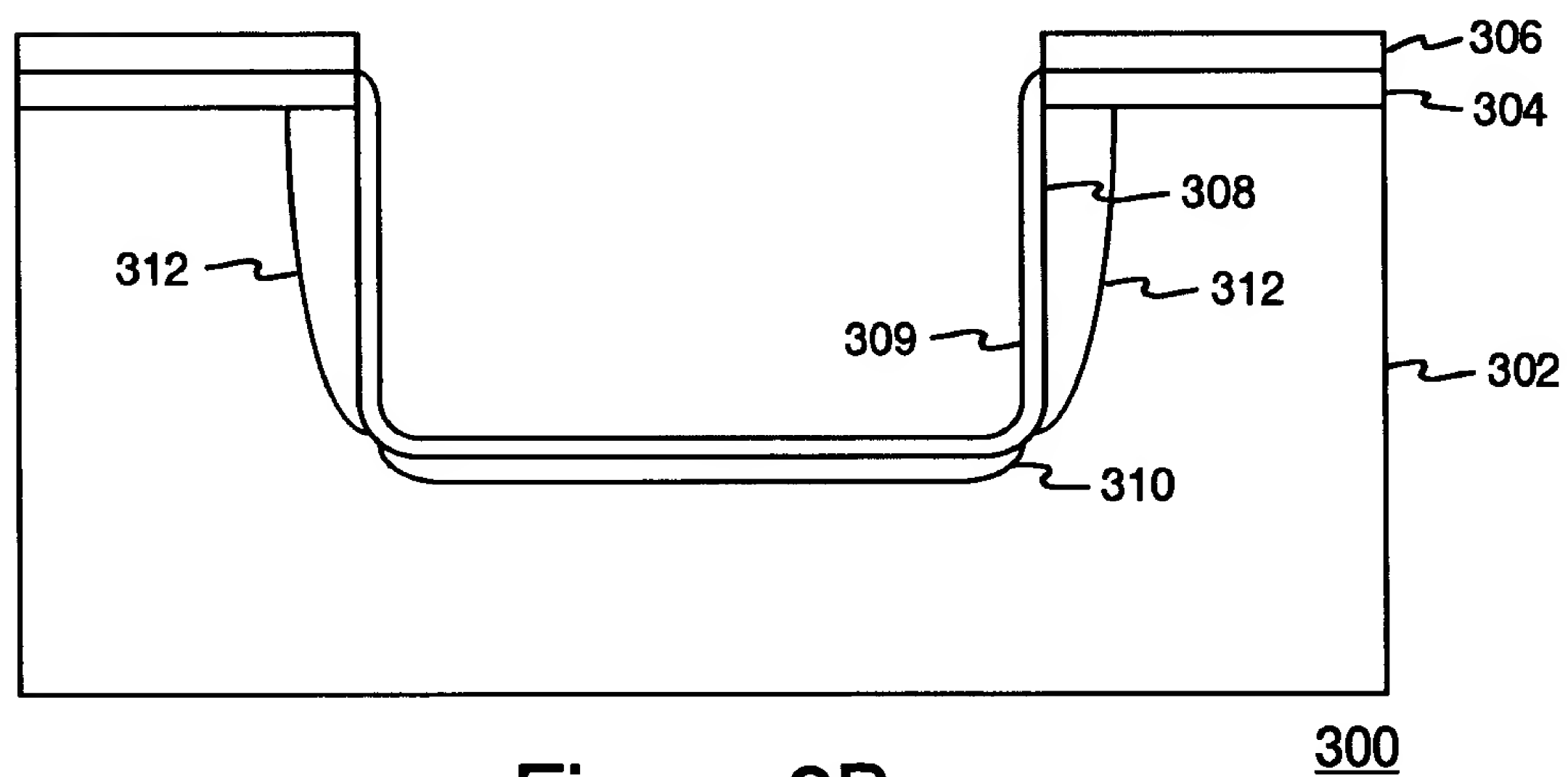


Figure 3B

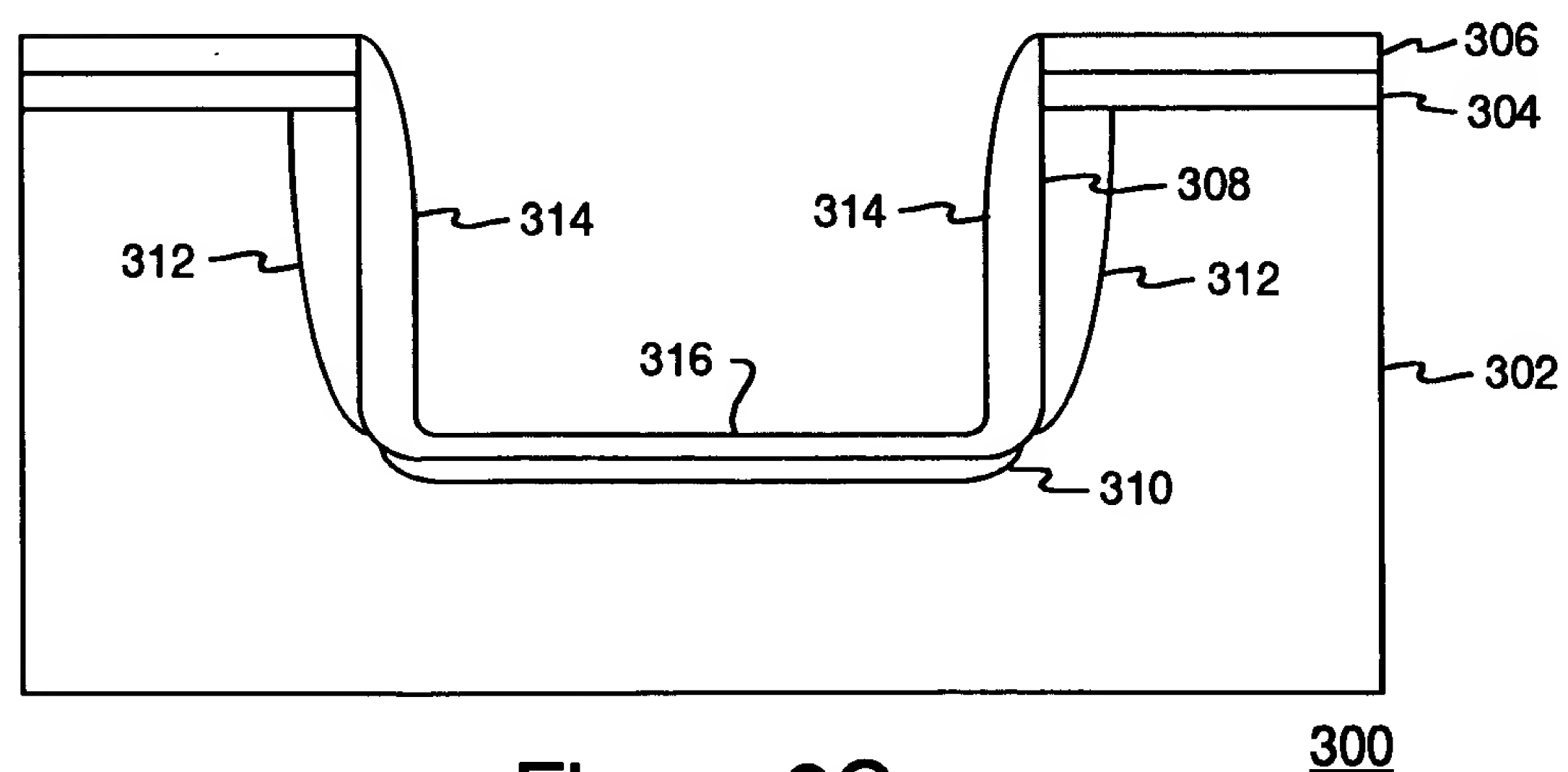


Figure 3C



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4 / 8

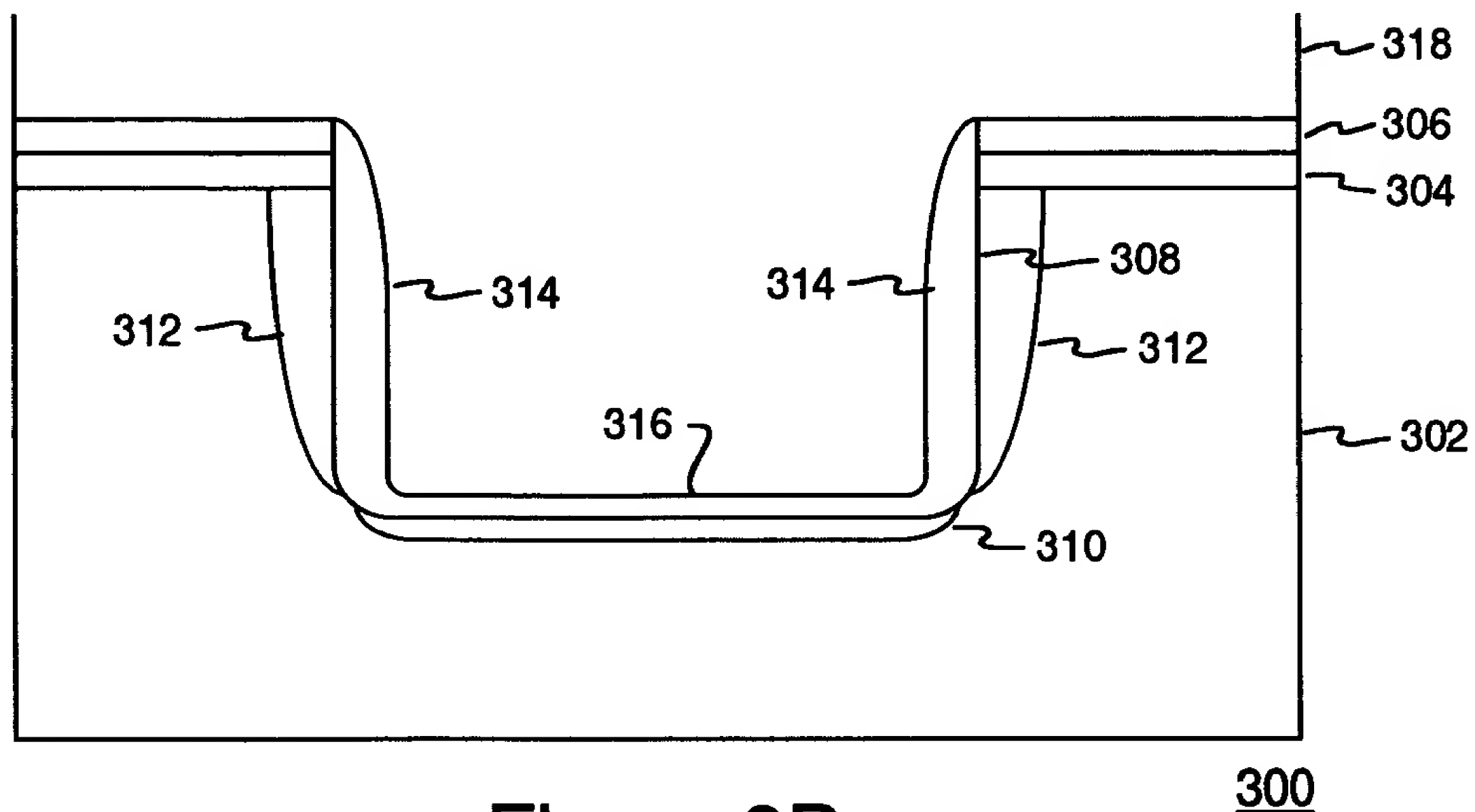


Figure 3D

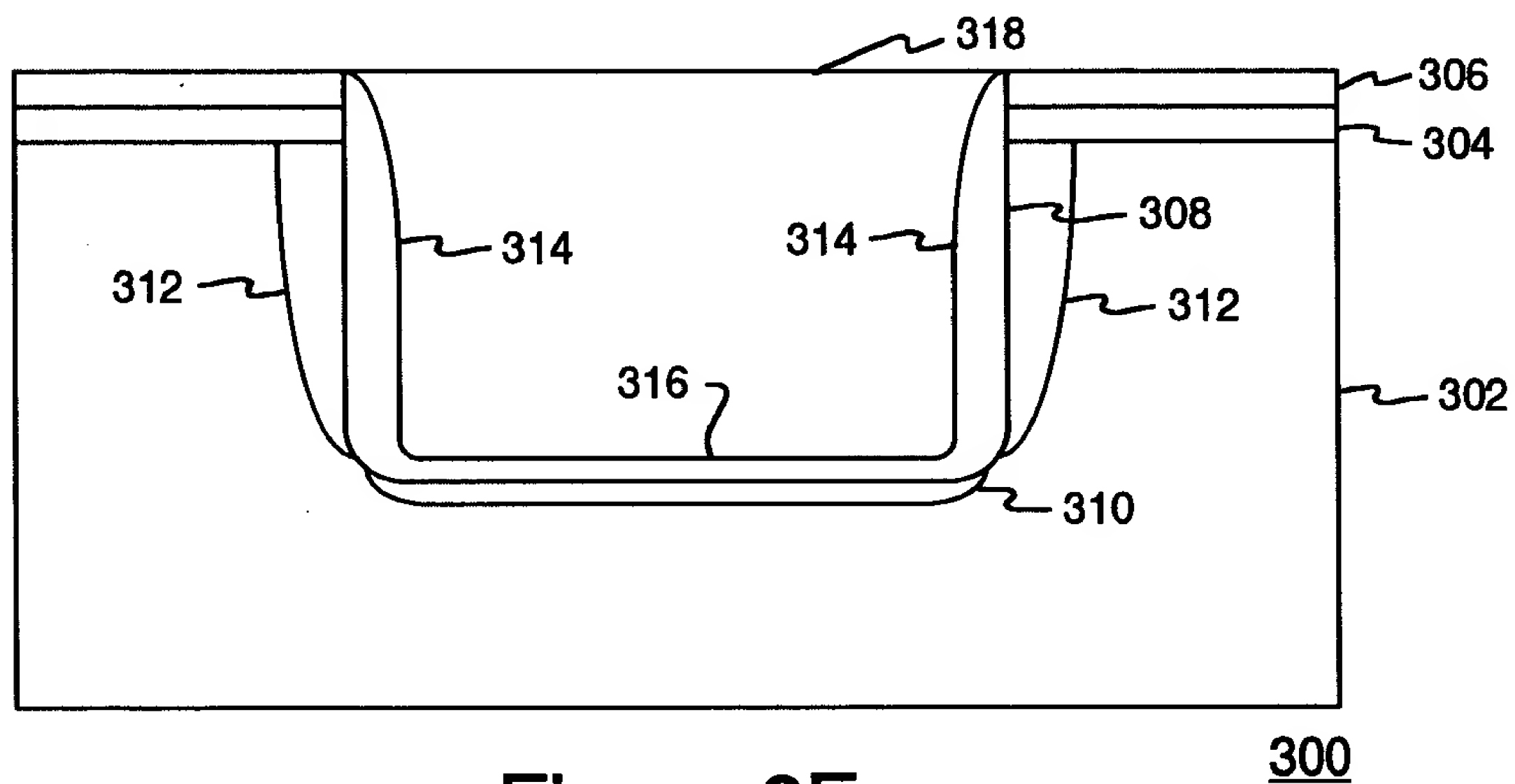


Figure 3E

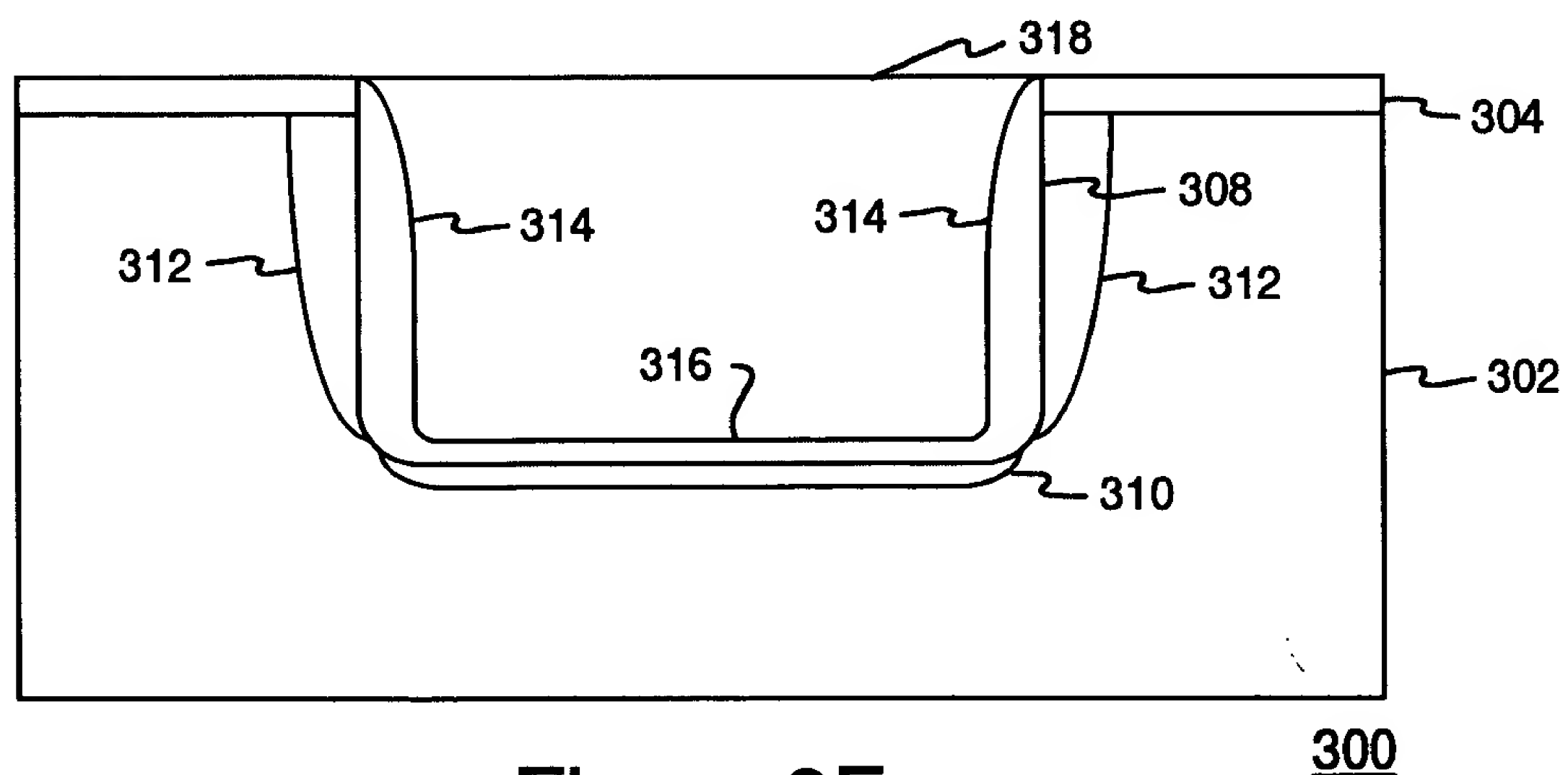


Figure 3F



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5 / 8

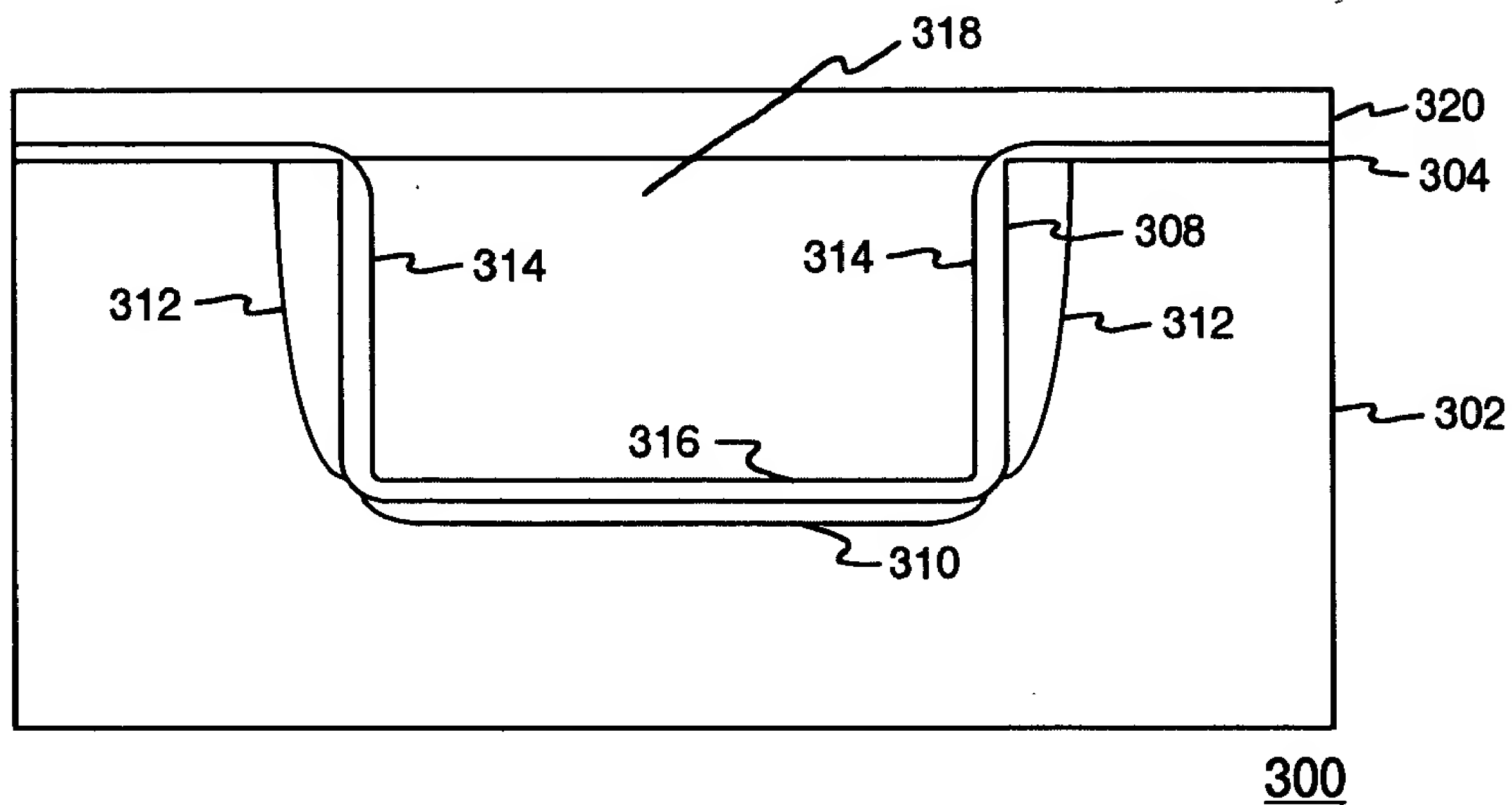


Figure 3G

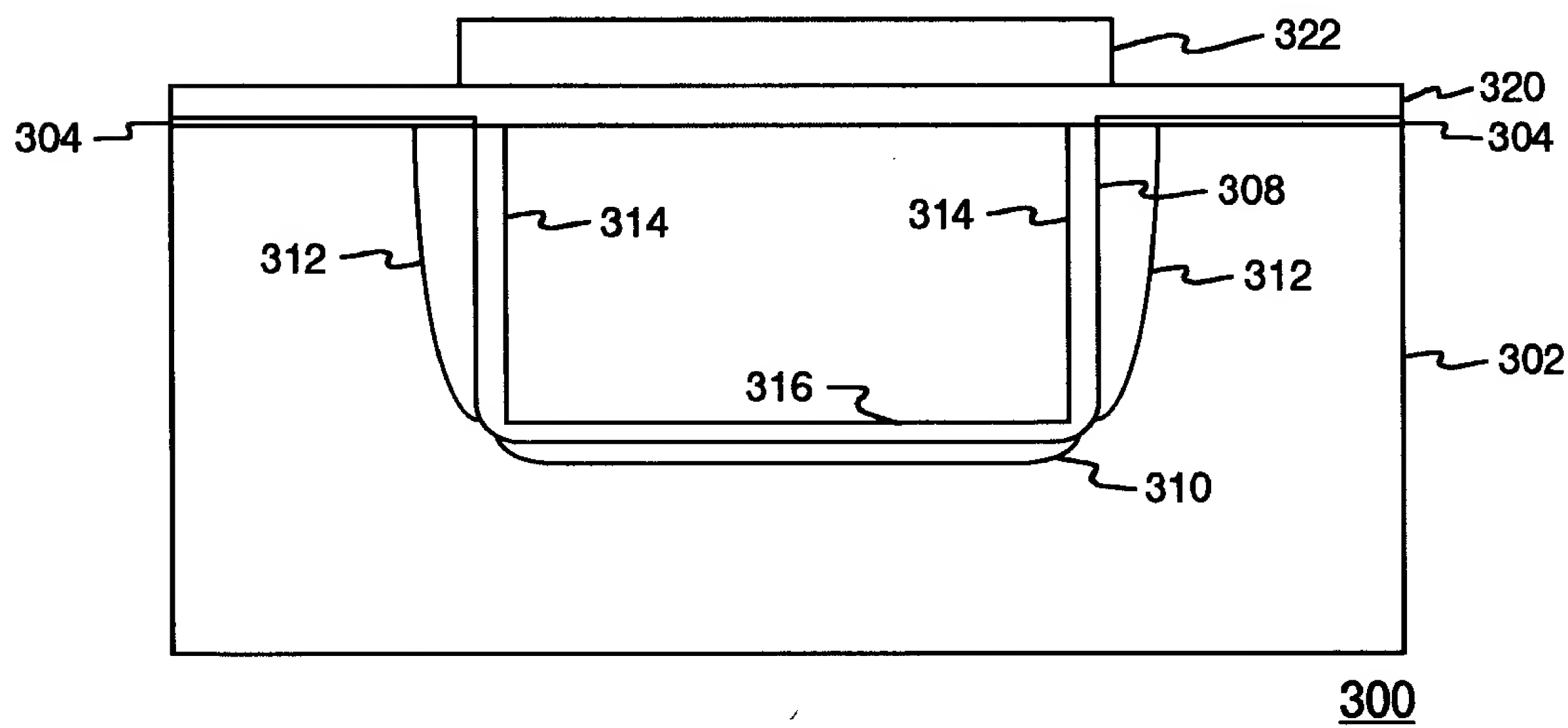


Figure 3H



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6 / 8

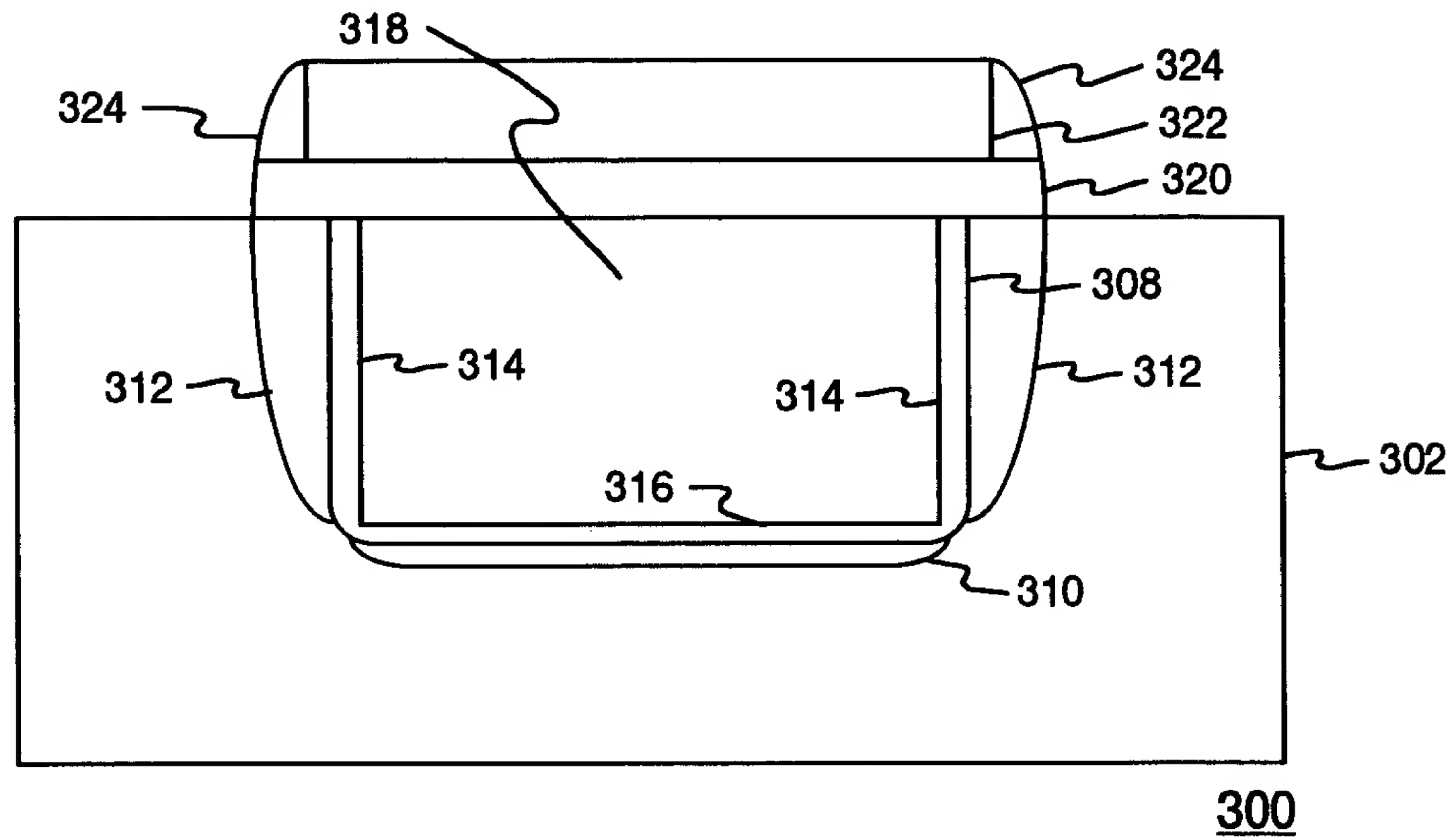


Figure 3I

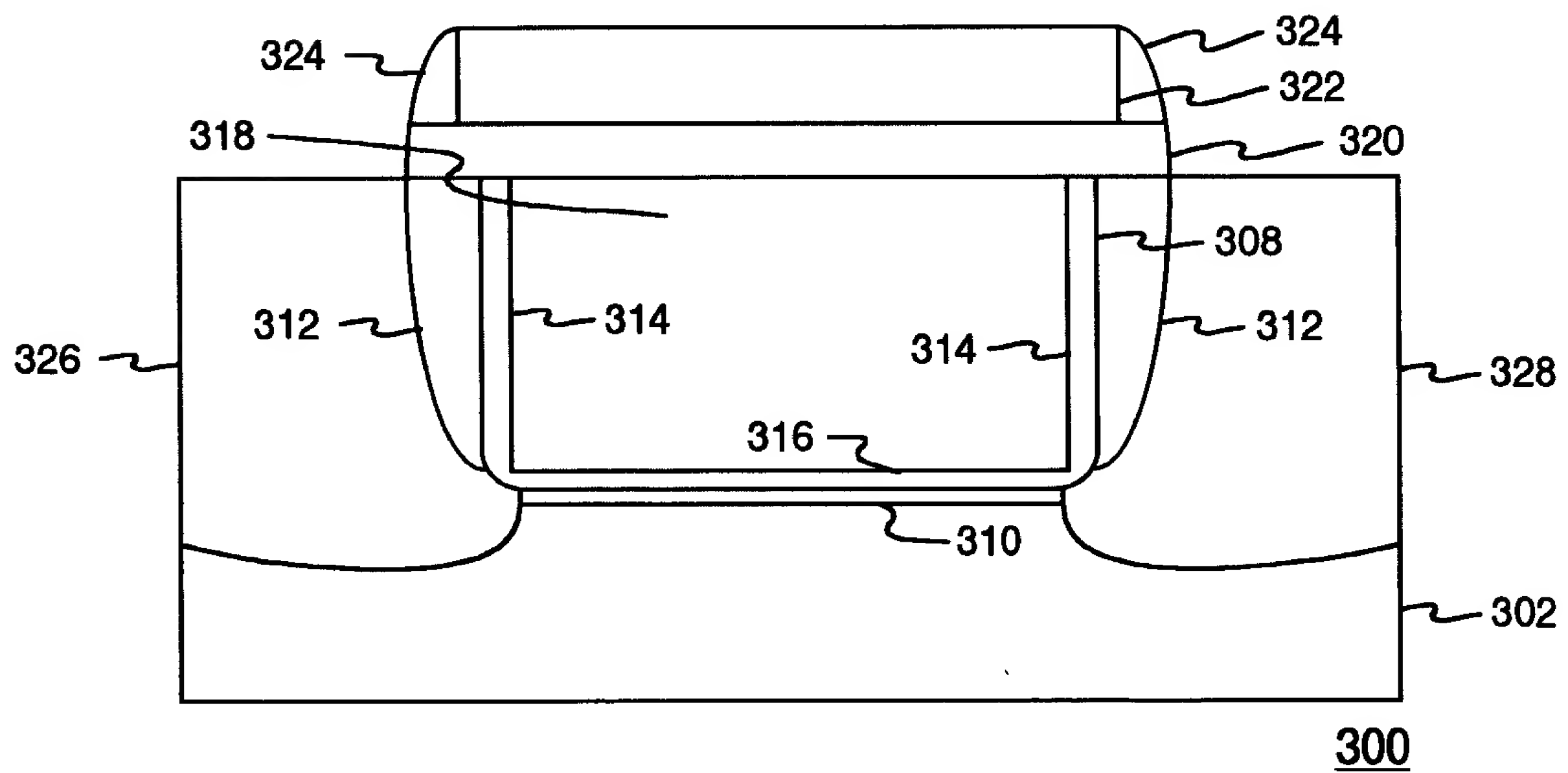


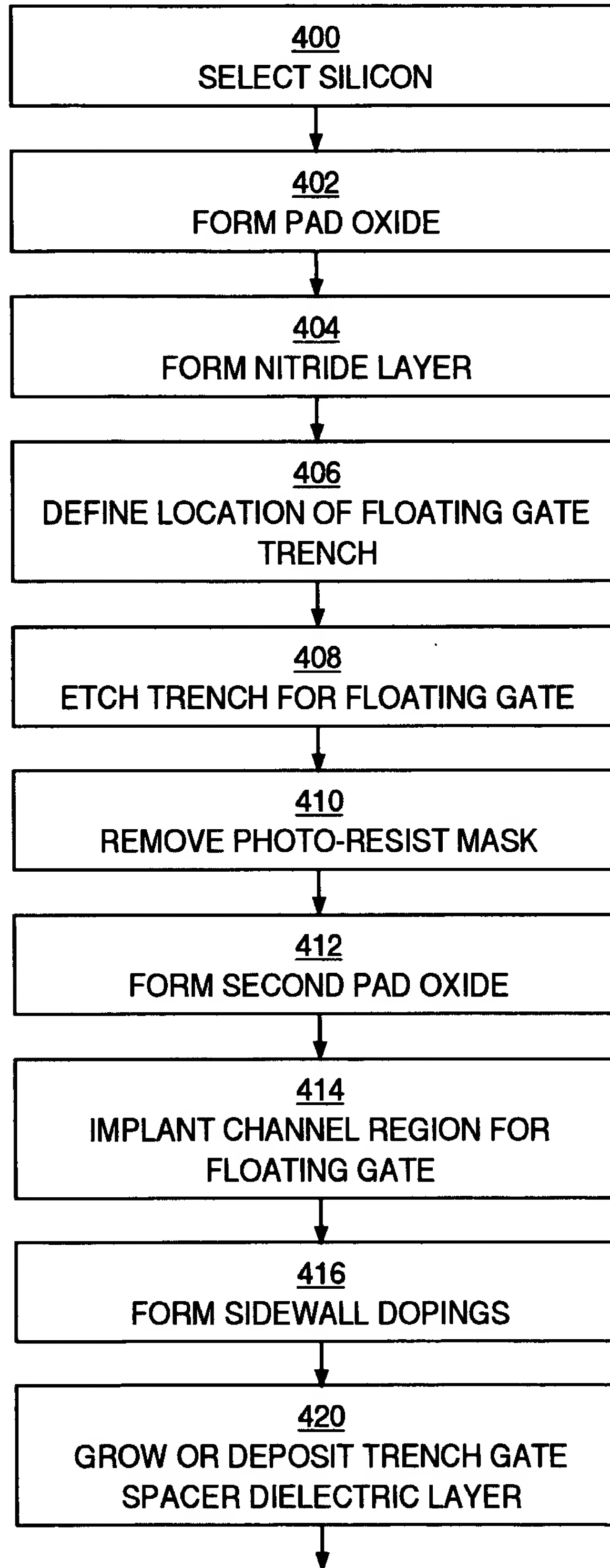
Figure 3J



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7 / 8



To Figure 4B

Figure 4A



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8 / 8

From Figure 4A

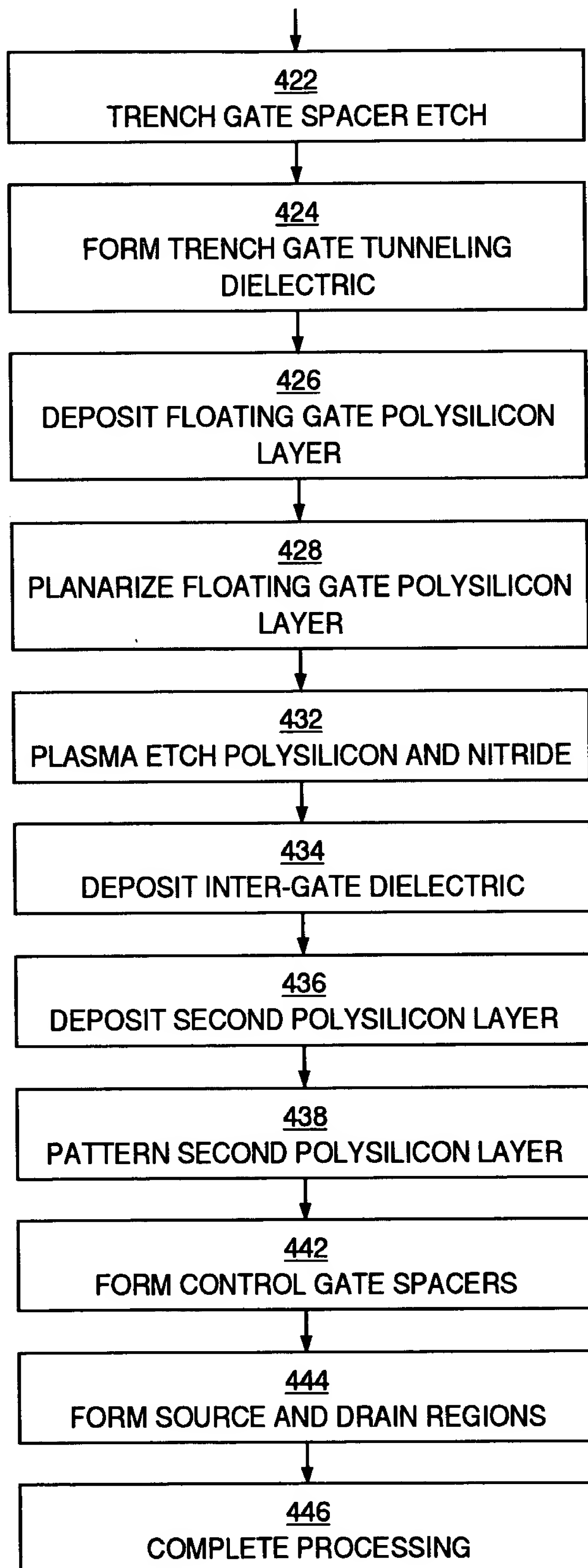


Figure 4B